TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MET574AFK

Octal D-Type Flip-Flop with 3-State Output

The TC7MET574AFK is an advanced high speed CMOS octal flip-flop with 3-state output fabricated with silicon gate $\rm C^2MOS$ technology.

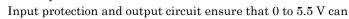
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type flip-flop is controlled by a clock input (CK) and a output enable input (\overline{OE}) .

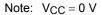
When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The input voltage are compatible with TTL output voltage.

This device may be used as a level converter for interfacing $3.3\ V$ to $5\ V$ system.



be applied to the input and output (Note) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

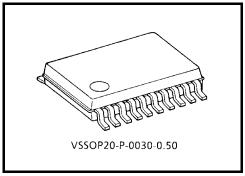


Features

- High speed: $f_{max} = 140 \text{ MHz (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- Compatible with TTL outputs: $V_{IL} = 0.8 \text{ V (max)}$

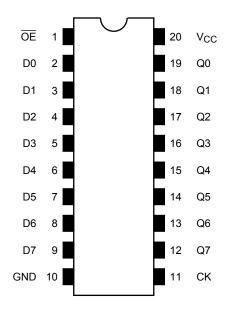
$$V_{IH} = 2.0 \text{ V (min)}$$

- · Power down protection is provided on all inputs and outputs.
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Low noise: VOLP = 1.5 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 574 type.

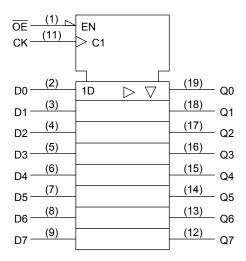


Weight: 0.03 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

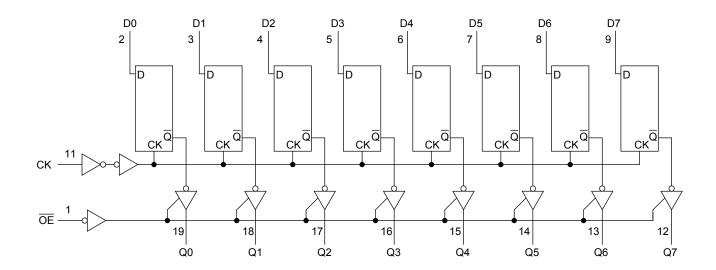
	Outputs		
ŌĒ	CK	Outputs	
Н	Х	Х	Z
L	$\overline{}$	Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q_n: No change

System Diagram





Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	Vout	−0.5~7.0 (Note 2)	V
DC output voltage	VOUI	-0.5~V _{CC} + 0.5 (Note 3)	V
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20 (Note 4)	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Output is off-state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5~5.5	V
Input voltage	V _{IN}	0~5.5	٧
Output voltage	\/	0~5.5 (Note 2)	V
Output voltage	V _{OUT}	0~V _{CC} (Note 3)	V
Operating temperature	T _{opr}	−40~85	°C
Input rise and fall time	dt/dv	0~20	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: Output in off state

Note 3: High or low state

Electrical Characteristics

DC Characteristics

Characteristics		Cumbal	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
		Symbol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
Input voltage	High level	V_{IH}		_	4.5~5.5	2.0	_	_	2.0	_	V
input voitage	Low level	V _{IL}		_	4.5~5.5	_	_	0.8	_	0.8	V
	High lovel	\/a	V _{IN} = V _{IH}	I _{OH} = -50 μA	4.5	4.4	4.5	_	4.4	_	V
Output voltage Low level	nigii ievei	VoH	or V _{IL}	I _{OH} = –8 mA	4.5	3.94	_	_	3.80	_	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	4.5	_	0	0.1	_	0.1	
				I _{OL} = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output of	3-state output off-state current I_{OZ} $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	_	±0.25	_	±2.50	μА		
Input leakage cu	ırrent	I _{IN}	V _{IN} = 5.5	V or GND	0~5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent supply current		Icc	V _{IN} = V _{CC} or GND		5.5	_	_	4.0	_	40.0	μΑ
		Ісст	Per input: V _{IN} = 3.4 V Other input: V _{CC} or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage	current	I _{OPD}	V _{OUT} = 5.5 V		0	_	_	0.5		5.0	μА

Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol Test Condition			Ta = 25°C		Ta = -40~85°C	Unit
	Symbol	rest Condition	V _{CC} (V)	Тур.	Limit	Limit	Offic
Minimum pulse width (CK)	t _{w (H)} t _{w (L)}	_	5.0 ± 0.5	_	6.5	8.5	ns
Minimum set-up time	ts	_	5.0 ± 0.5	_	2.5	2.5	ns
Minimum hold time	t _h		5.0 ± 0.5	_	2.5	2.5	ns



AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -4	Unit	
Onar acteristics Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Oill	
Propagation delay time	t _{pLH}		5.0 ±	15	_	4.1	9.4	1.0	10.5	ns
(CK-Q)	tpHL	_	0.5	50		5.6	10.4	1.0	11.5	110
3 state output enable time	t _{pZL}	P 1 kO	5.0 ±	15		6.5	10.2	1.0	11.5	
3-state output enable time $\begin{cases} t_{pZL} \\ t_{pZH} \end{cases}$ $R_{L} = 1 \text{ k}\Omega$	N_	0.5	50		7.3	11.2	1.0	12.5	ns	
3-state output disable time	t _{pLZ} t _{pHZ}	$R_L = 1 \text{ k}\Omega$	5.0 ± 0.5	50		7.0	11.2	1.0	12.0	ns
Maximum clock frequency	£		5.0 ±	15	90	140	_	80	_	MHz
Maximum clock frequency	f _{max}	_	0.5	50	85	130		75		IVITIZ
Output to output skew	t _{osLH} t _{osHL}	(Note 1)	5.0 ± 0.5	50		_	1.0		1.0	ns
Input capacitance	C _{IN}	_	_		_	4	10	_	10	pF
Output capacitance	C _{OUT}	_	-			9		_		pF
Power dissipation capacitance	C _{PD}			(Note 2)		25		_		pF

Note 1: Parameter guaranteed by design.

 $t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$

And the total CPD when n pcs. of latch operate can be gained by the following equation:

 C_{PD} (total) = 14 + 11 · n

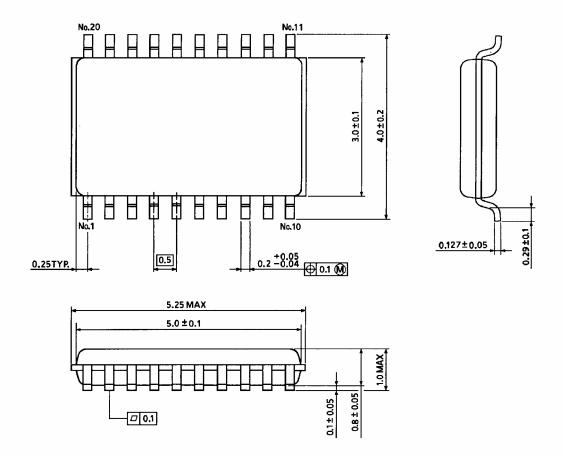
Noise Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	1.1	1.5	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-1.1	-1.5	V
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	C _L = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	0.8	V

5 2007-10-19



Package Dimensions



Weight: 0.03 g (typ.)

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
 compatibility. Please use these products in this document in compliance with all applicable laws and regulations
 that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
 occurring as a result of noncompliance with applicable laws and regulations.